

Switch-mode Power Rectifier 100 V, 30 A

MBR30H100CTG, MBRF30H100CTG

Features and Benefits

- Low Forward Voltage: 0.67 V @ 125°C
- Low Power Loss/High Efficiency
- High Surge Capacity
- 175°C Operating Junction Temperature
- 30 A Total (15 A Per Diode Leg)
- These are Pb-Free Devices

Applications

- Power Supply – Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics:

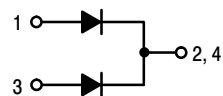
- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model = 3B
Machine Model = C



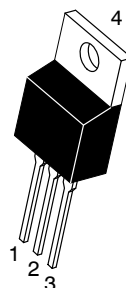
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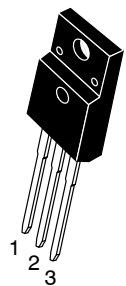
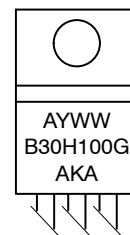
SCHOTTKY BARRIER RECTIFIER 30 AMPERES 100 VOLTS



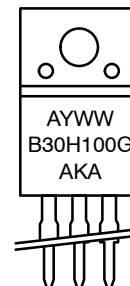
MARKING DIAGRAMS



TO-220
CASE 221A
STYLE 6



TO-220 FULLPAK
CASE 221D



A = Assembly Location
Y = Year
WW = Work Week
B30H100 = Device Code
G = Pb-Free Package
AKA = Polarity Designator

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MBR30H100CTG, MBRF30H100CTG

MAXIMUM RATINGS (Per Diode Leg)

| Rating | Symbol | Value | Unit |
|--|---------------------------------|-----------------|------------------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | V_{RRM} V_{RWM} V_R | 100 | V |
| Average Rectified Forward Current ($T_C = 156^\circ\text{C}$) Per Diode Per Device | $I_{F(AV)}$ | 15 30 | A |
| Peak Repetitive Forward Current (Square Wave, 20 kHz, $T_C = 151^\circ\text{C}$) | I_{FM} | 30 | A |
| Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz) | I_{FSM} | 250 | A |
| Operating Junction Temperature (Note 1) | T_J | +175 | $^\circ\text{C}$ |
| Storage Temperature | T_{stg} | -65 to +175 | $^\circ\text{C}$ |
| Voltage Rate of Change (Rated V_R) | dv/dt | 10,000 | V/ μs |
| Controlled Avalanche Energy (see test conditions in Figures 13 and 14) | W_{AVAIL} | 200 | mJ |
| ESD Ratings: Machine Model = C Human Body Model = 3B | | > 400 > 8000 | V |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Value | Unit |
|---|--|------------------------|---------------------------|
| Maximum Thermal Resistance (MBR30H100CTG) - Junction-to-Case - Junction-to-Ambient (MBRF30H100CTG) - Junction-to-Case - Junction-to-Ambient | $R_{\theta JC}$ $R_{\theta JA}$ $R_{\theta JC}$ $R_{\theta JA}$ | 2.0 60 4.2 75 | $^\circ\text{C}/\text{W}$ |

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|--|--------|------------------|------------------------------|------------------------------|------|
| Maximum Instantaneous Forward Voltage (Note 2) ($i_F = 15\text{ A}$, $T_J = 25^\circ\text{C}$) ($i_F = 15\text{ A}$, $T_J = 125^\circ\text{C}$) ($i_F = 30\text{ A}$, $T_J = 25^\circ\text{C}$) ($i_F = 30\text{ A}$, $T_J = 125^\circ\text{C}$) | V_F | - - - - | 0.76 0.64 0.88 0.76 | 0.80 0.67 0.93 0.80 | V |
| Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, $T_J = 125^\circ\text{C}$) (Rated DC Voltage, $T_J = 25^\circ\text{C}$) | i_R | - - | 1.1 0.0008 | 6.0 0.0045 | mA |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

ORDERING INFORMATION

| Device Order Number | Package Type | Shipping [†] |
|---------------------|-----------------------|-----------------------|
| MBR30H100CTG | TO-220 (Pb-Free) | 50 Units / Rail |
| MBRF30H100CTG | TO-220FP (Pb-Free) | 50 Units / Rail |

MBR30H100CTG, MBRF30H100CTG

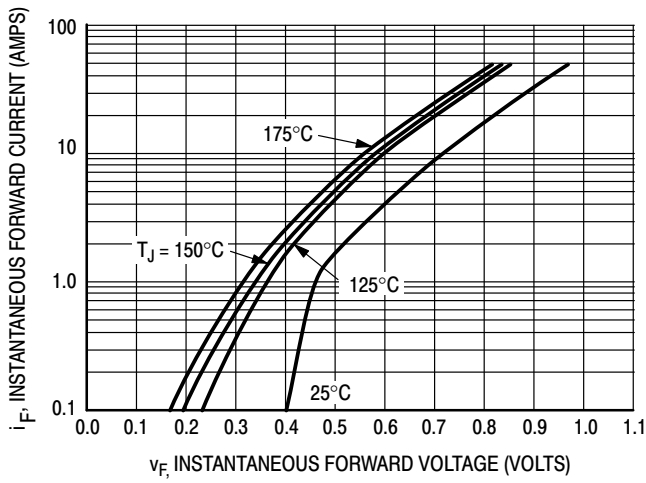


Figure 1. Typical Forward Voltage

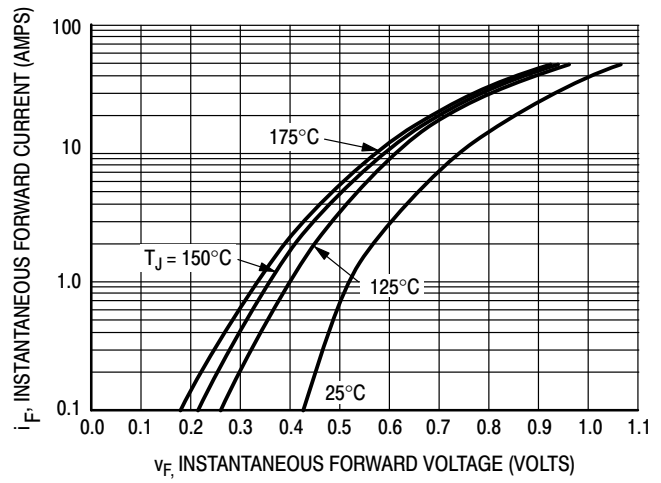


Figure 2. Maximum Forward Voltage

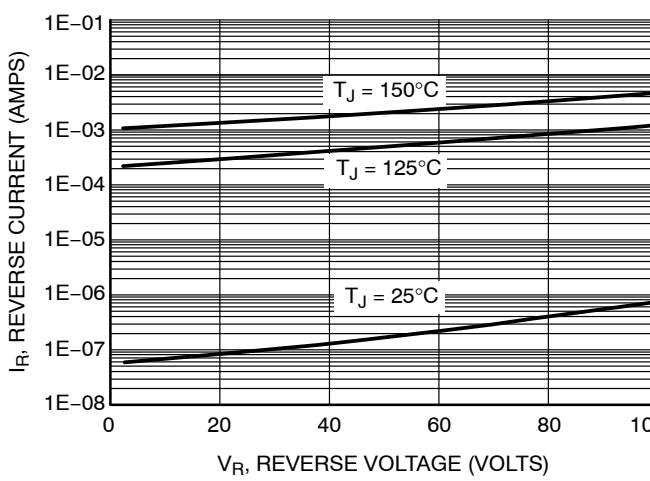


Figure 3. Typical Reverse Current

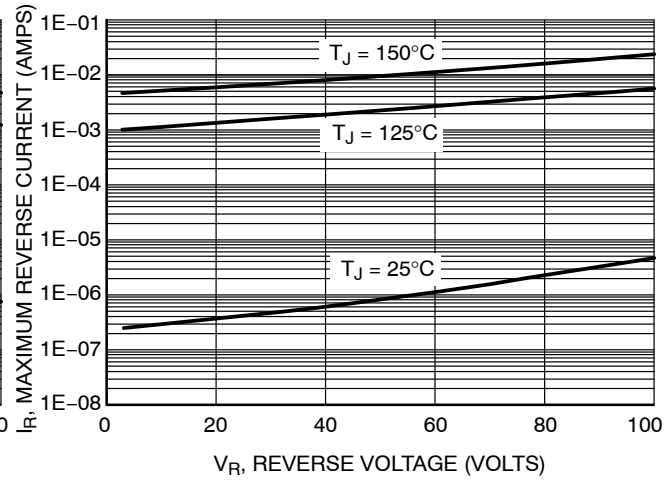


Figure 4. Maximum Reverse Current

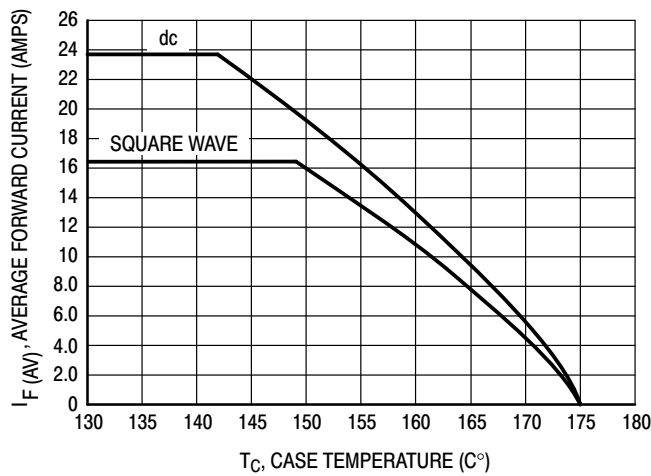


Figure 5. Current Derating, Case Per Leg

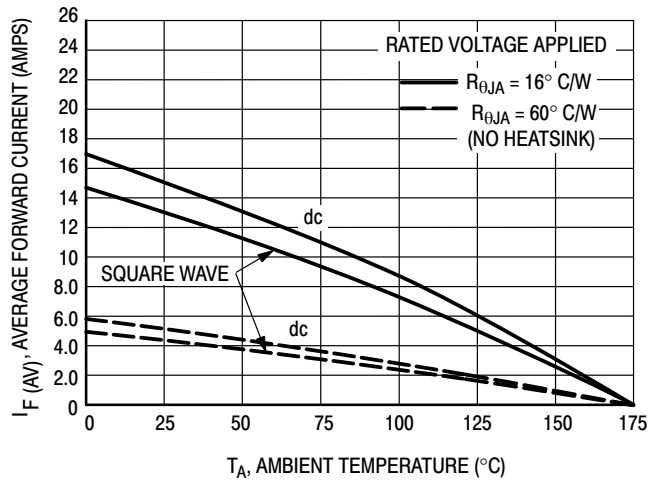


Figure 6. Current Derating, Ambient Per Leg

MBR30H100CTG, MBRF30H100CTG

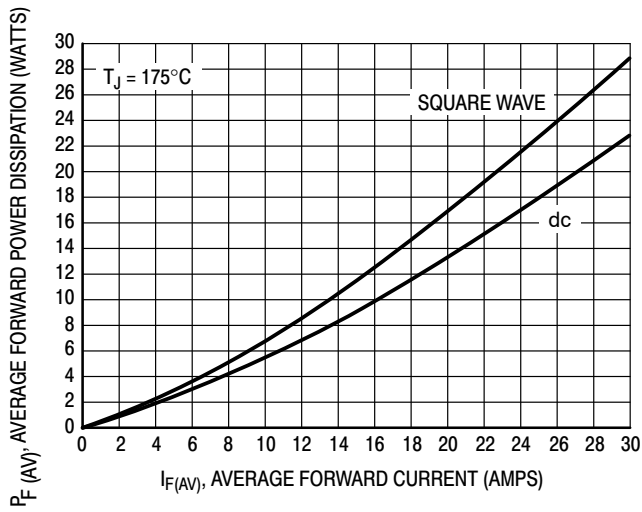


Figure 7. Forward Power Dissipation

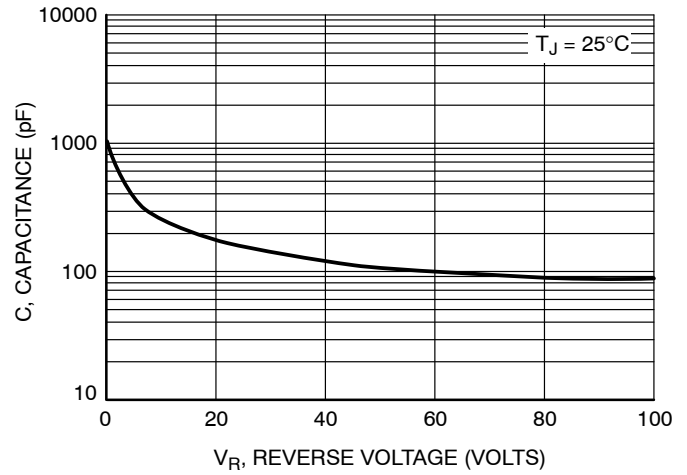


Figure 8. Capacitance

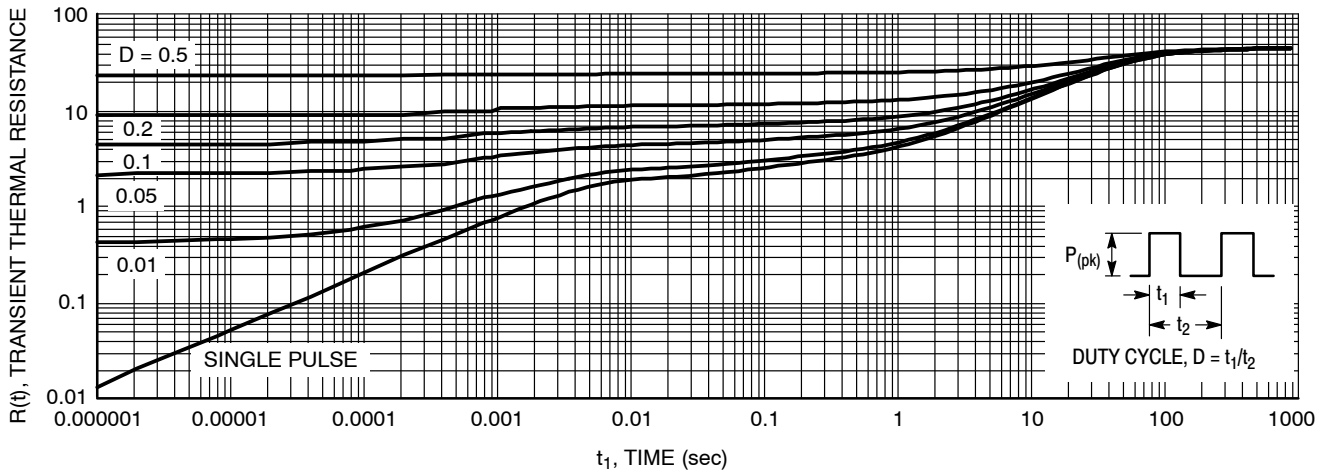


Figure 9. Thermal Response Junction-to-Ambient for MBR30H100CT

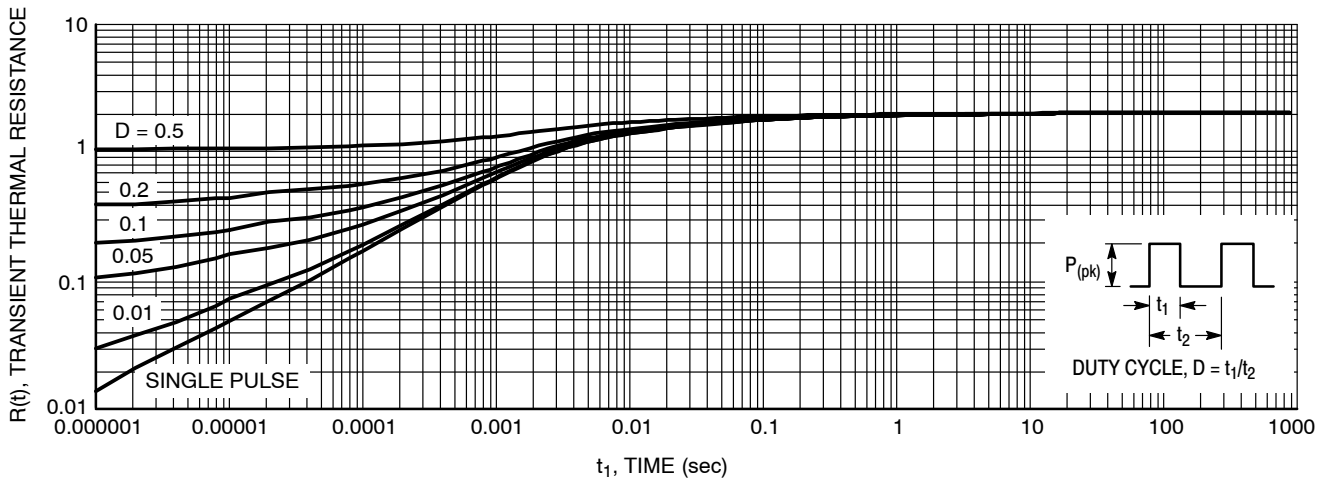


Figure 10. Thermal Response Junction-to-Case for MBR30H100CT

MBR30H100CTG, MBRF30H100CTG

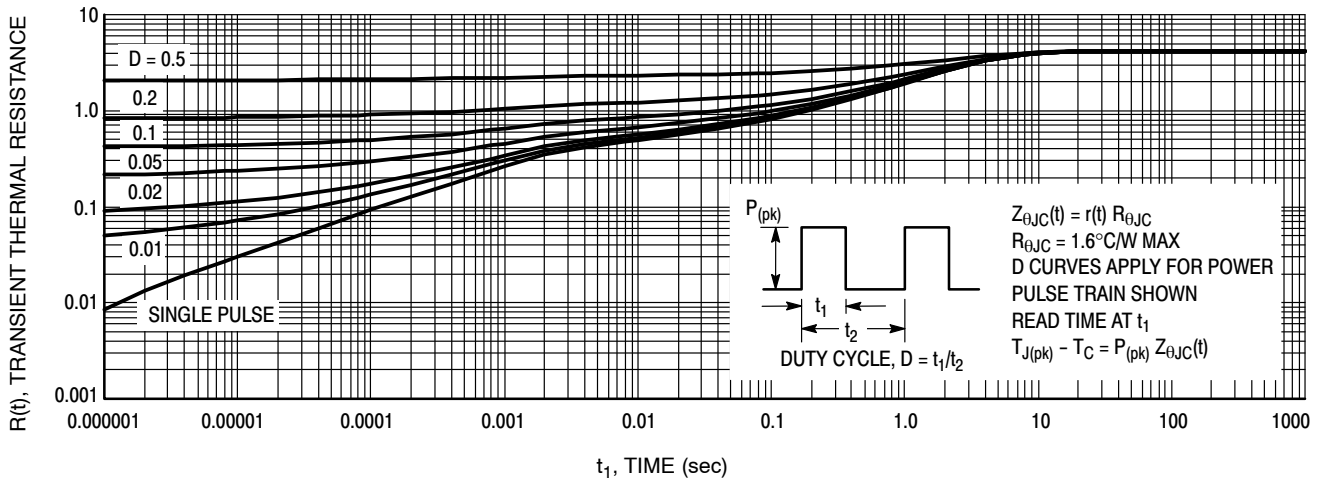


Figure 11. Thermal Response Junction-to-Case for MBRF30H100CT

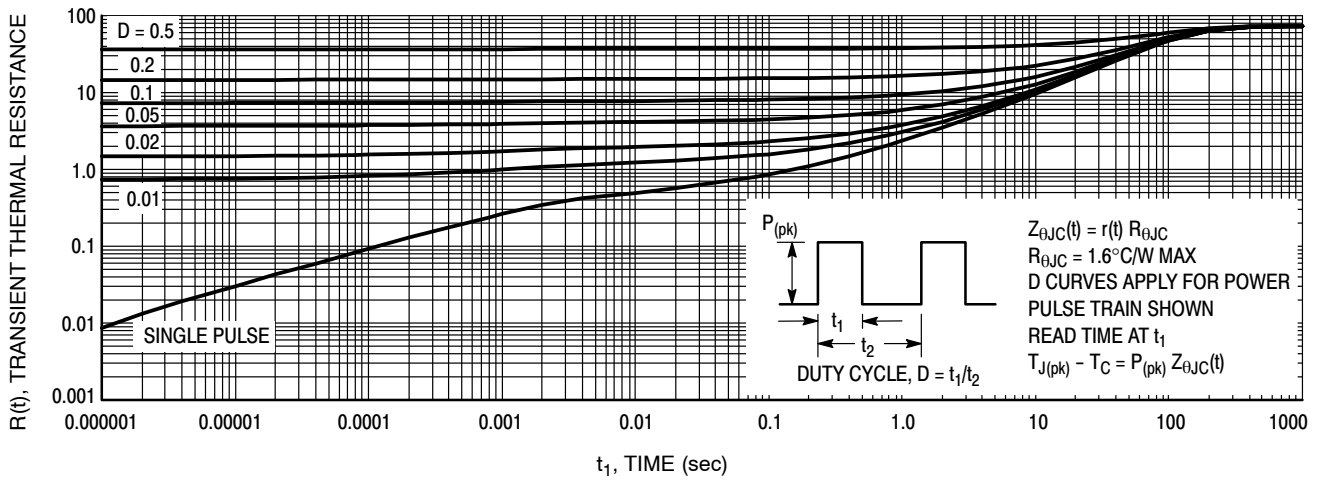


Figure 12. Thermal Response Junction-to-Ambient for MBRF30H100CT

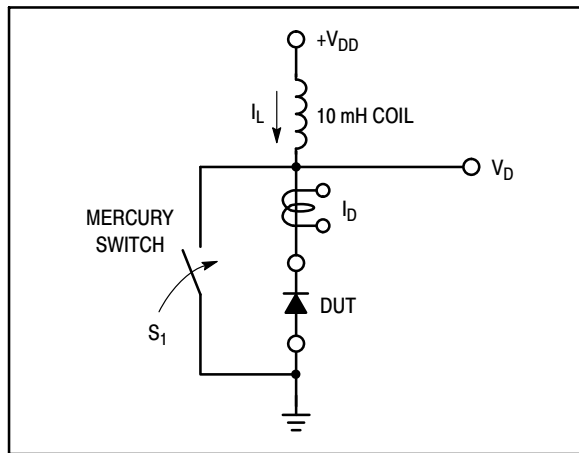


Figure 13. Test Circuit

The unclamped inductive switching circuit shown in Figure 13 was used to demonstrate the controlled avalanche capability of this device. A mercury switch was used instead of an electronic switch to simulate a noisy environment when the switch was being opened.

When S_1 is closed at t_0 the current in the inductor I_L ramps up linearly; and energy is stored in the coil. At t_1 the switch is opened and the voltage across the diode under test begins to rise rapidly, due to di/dt effects, when this induced voltage reaches the breakdown voltage of the diode, it is clamped at BV_{DUT} and the diode begins to conduct the full load current which now starts to decay linearly through the diode, and goes to zero at t_2 .

By solving the loop equation at the point in time when S_1 is opened; and calculating the energy that is transferred to the diode it can be shown that the total energy transferred is equal to the energy stored in the inductor plus a finite amount of energy from the V_{DD} power supply while the diode is in breakdown (from t_1 to t_2) minus any losses due to finite component resistances. Assuming the component resistive

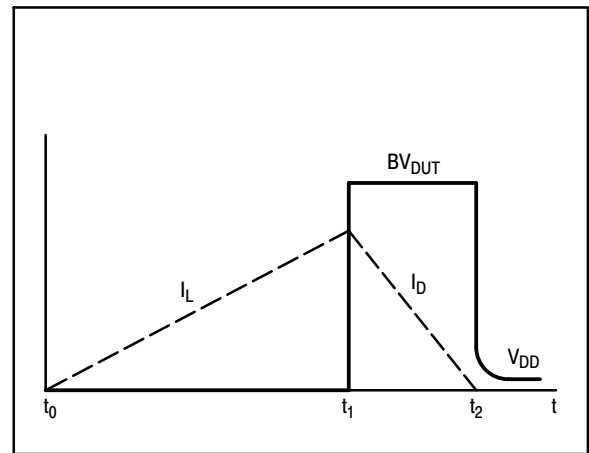


Figure 14. Current-Voltage Waveforms

elements are small Equation (1) approximates the total energy transferred to the diode. It can be seen from this equation that if the V_{DD} voltage is low compared to the breakdown voltage of the device, the amount of energy contributed by the supply during breakdown is small and the total energy can be assumed to be nearly equal to the energy stored in the coil during the time when S_1 was closed, Equation (2).

EQUATION (1):

$$W_{AVAL} \approx \frac{1}{2} L I_{LPK}^2 \left(\frac{BV_{DUT}}{BV_{DUT} - V_{DD}} \right)$$

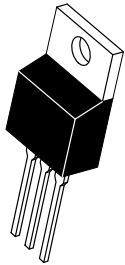
EQUATION (2):

$$W_{AVAL} \approx \frac{1}{2} L I_{LPK}^2$$

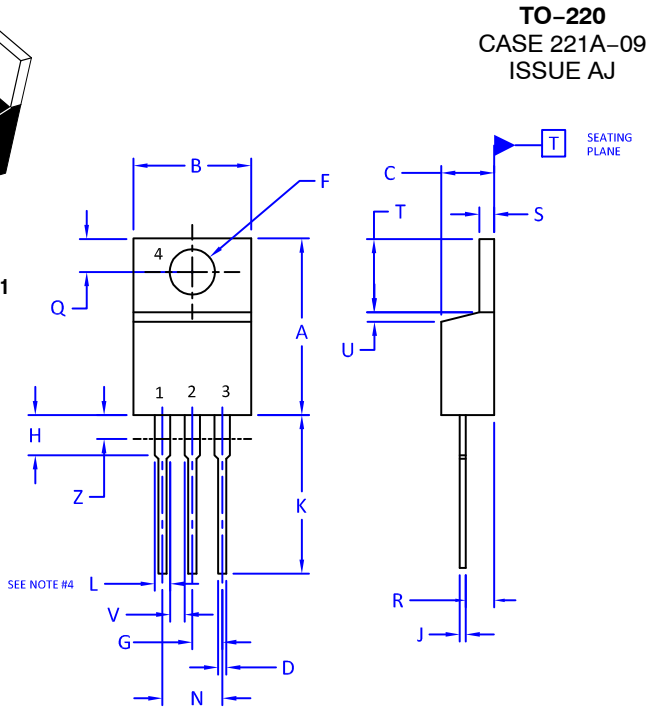
MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 1:1



TO-220
CASE 221A-09
ISSUE AJ

DATE 05 NOV 2019

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 0.570 | 0.620 | 14.48 | 15.75 |
| B | 0.380 | 0.415 | 9.66 | 10.53 |
| C | 0.160 | 0.190 | 4.07 | 4.83 |
| D | 0.025 | 0.038 | 0.64 | 0.96 |
| F | 0.142 | 0.161 | 3.60 | 4.09 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| H | 0.110 | 0.161 | 2.80 | 4.10 |
| J | 0.014 | 0.024 | 0.36 | 0.61 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.41 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| V | 0.045 | --- | 1.15 | --- |
| Z | --- | 0.080 | --- | 2.04 |

STYLE 1:

- PIN 1. BASE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

STYLE 2:

- PIN 1. BASE
- 2. EMITTER
- 3. COLLECTOR
- 4. EMITTER

STYLE 3:

- PIN 1. CATHODE
- 2. ANODE
- 3. GATE
- 4. ANODE

STYLE 4:

- PIN 1. MAIN TERMINAL 1
- 2. MAIN TERMINAL 2
- 3. GATE
- 4. MAIN TERMINAL 2

STYLE 5:

- PIN 1. GATE
- 2. DRAIN
- 3. SOURCE
- 4. DRAIN

STYLE 6:

- PIN 1. ANODE
- 2. CATHODE
- 3. ANODE
- 4. CATHODE

STYLE 7:

- PIN 1. CATHODE
- 2. ANODE
- 3. CATHODE
- 4. ANODE

STYLE 8:

- PIN 1. CATHODE
- 2. ANODE
- 3. EXTERNAL TRIP/DELAY
- 4. ANODE

STYLE 9:

- PIN 1. GATE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

STYLE 10:

- PIN 1. GATE
- 2. SOURCE
- 3. DRAIN
- 4. SOURCE

STYLE 11:

- PIN 1. DRAIN
- 2. SOURCE
- 3. GATE
- 4. SOURCE

STYLE 12:

- PIN 1. MAIN TERMINAL 1
- 2. MAIN TERMINAL 2
- 3. GATE
- 4. NOT CONNECTED

| | | |
|------------------|-------------|--|
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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

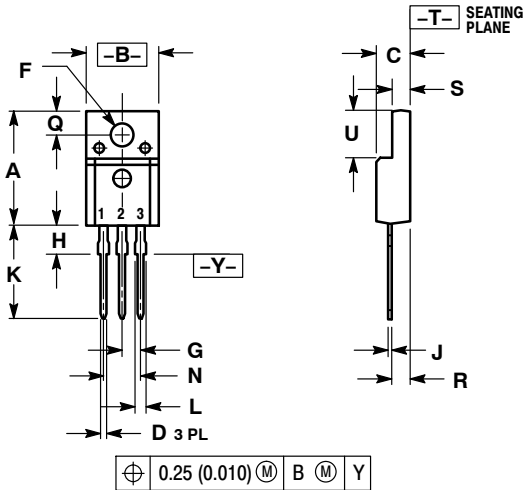
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SCALE 1:1

TO-220 FULLPAK CASE 221D-03 ISSUE K

DATE 27 FEB 2009



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH
 3. 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

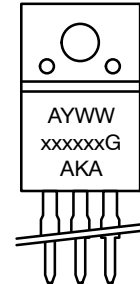
| DIM | INCHES | | MILLIMETERS | |
|-----|-----------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.617 | 0.635 | 15.67 | 16.12 |
| B | 0.392 | 0.419 | 9.96 | 10.63 |
| C | 0.177 | 0.193 | 4.50 | 4.90 |
| D | 0.024 | 0.039 | 0.60 | 1.00 |
| F | 0.116 | 0.129 | 2.95 | 3.28 |
| G | 0.100 BSC | | 2.54 BSC | |
| H | 0.118 | 0.135 | 3.00 | 3.43 |
| J | 0.018 | 0.025 | 0.45 | 0.63 |
| K | 0.503 | 0.541 | 12.78 | 13.73 |
| L | 0.048 | 0.058 | 1.23 | 1.47 |
| N | 0.200 BSC | | 5.08 BSC | |
| Q | 0.122 | 0.138 | 3.10 | 3.50 |
| R | 0.099 | 0.117 | 2.51 | 2.96 |
| S | 0.092 | 0.113 | 2.34 | 2.87 |
| U | 0.239 | 0.271 | 6.06 | 6.88 |

MARKING DIAGRAMS

- | | | |
|--|---|--|
| STYLE 1: PIN 1. GATE 2. DRAIN 3. SOURCE | STYLE 2: PIN 1. BASE 2. COLLECTOR 3. EMITTER | STYLE 3: PIN 1. ANODE 2. CATHODE 3. ANODE |
| STYLE 4: PIN 1. CATHODE 2. ANODE 3. CATHODE | STYLE 5: PIN 1. CATHODE 2. ANODE 3. GATE | STYLE 6: PIN 1. MT 1 2. MT 2 3. GATE |



Bipolar



Rectifier

- | | |
|-------------------------------|---------------------------|
| xxxxxx = Specific Device Code | A = Assembly Location |
| G = Pb-Free Package | Y = Year |
| A = Assembly Location | WW = Work Week |
| Y = Year | xxxxxx = Device Code |
| WW = Work Week | G = Pb-Free Package |
| | AKA = Polarity Designator |

| | | |
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